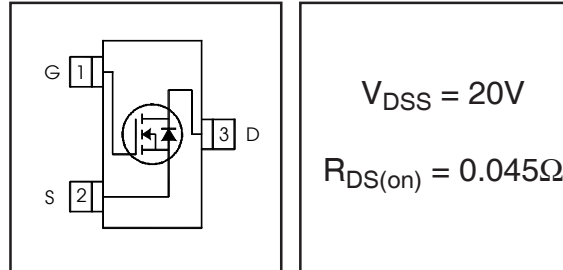


# IRLML2502PbF

HEXFET® Power MOSFET

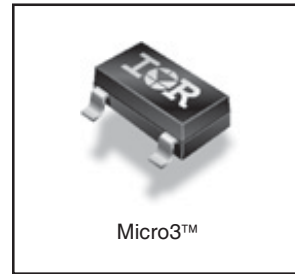
- Ultra Low On-Resistance
- N-Channel MOSFET
- SOT-23 Footprint
- Low Profile (<1.1mm)
- Available in Tape and Reel
- Fast Switching
- Lead-Free



## Description

These N-Channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET® power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in battery and load management.

A thermally enhanced large pad leadframe has been incorporated into the standard SOT-23 package to produce a HEXFET Power MOSFET with the industry's smallest footprint. This package, dubbed the Micro3™, is ideal for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro3 allows it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards. The thermal resistance and power dissipation are the best available.



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain- Source Voltage	20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	4.2	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	3.4	
$I_{DM}$	Pulsed Drain Current ①	33	
$P_D @ T_A = 25^\circ C$	Power Dissipation	1.25	W
$P_D @ T_A = 70^\circ C$	Power Dissipation	0.8	
	Linear Derating Factor	0.01	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 12$	V
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	°C

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	75	100	°C/W

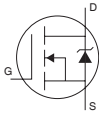
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International  
IR Rectifier

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.01	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	0.035	0.045	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4.2A ②
		—	0.050	0.080		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 3.6A ②
V <sub>GS(th)</sub>	Gate Threshold Voltage	0.60	—	1.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	5.8	—	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 4.0A
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	1.0	μA	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
		—	—	25		V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 70°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	-100	nA	V <sub>GS</sub> = -12V
	Gate-to-Source Reverse Leakage	—	—	100		V <sub>GS</sub> = 12V
Q <sub>g</sub>	Total Gate Charge	—	8.0	12	nC	I <sub>D</sub> = 4.0A
Q <sub>gs</sub>	Gate-to-Source Charge	—	1.8	2.7		V <sub>DS</sub> = 10V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	1.7	2.6		V <sub>GS</sub> = 5.0V ②
t <sub>d(on)</sub>	Turn-On Delay Time	—	7.5	—	ns	V <sub>DD</sub> = 10V
t <sub>r</sub>	Rise Time	—	10	—		I <sub>D</sub> = 1.0A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	54	—		R <sub>G</sub> = 6Ω
t <sub>f</sub>	Fall Time	—	26	—		R <sub>D</sub> = 10Ω ②
C <sub>iss</sub>	Input Capacitance	—	740	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	90	—		V <sub>DS</sub> = 15V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	66	—		f = 1.0MHz

## Source-Drain Ratings and Characteristics

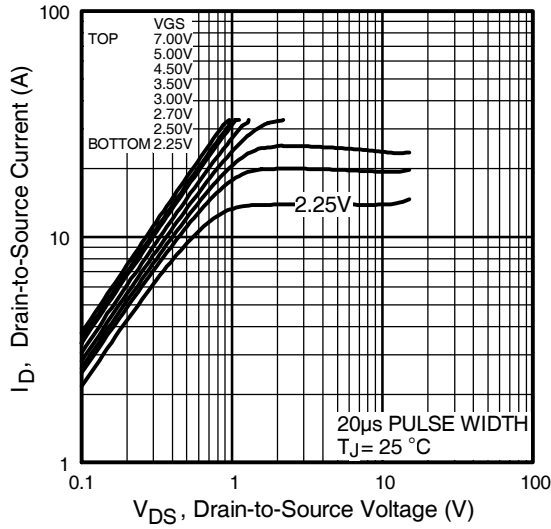
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	33		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.2	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 1.3A, V <sub>GS</sub> = 0V ②
t <sub>rr</sub>	Reverse Recovery Time	—	16	24	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 1.3A
Q <sub>rr</sub>	Reverse Recovery Charge	—	8.6	13	nC	di/dt = 100A/μs ②

### Notes:

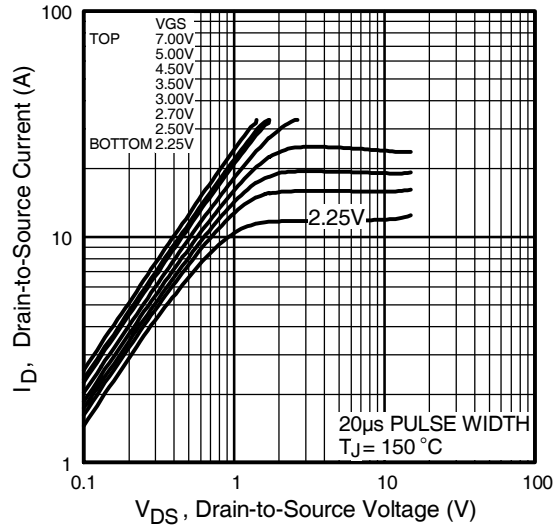
① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )

② Pulse width ≤ 300μs; duty cycle ≤ 2%.

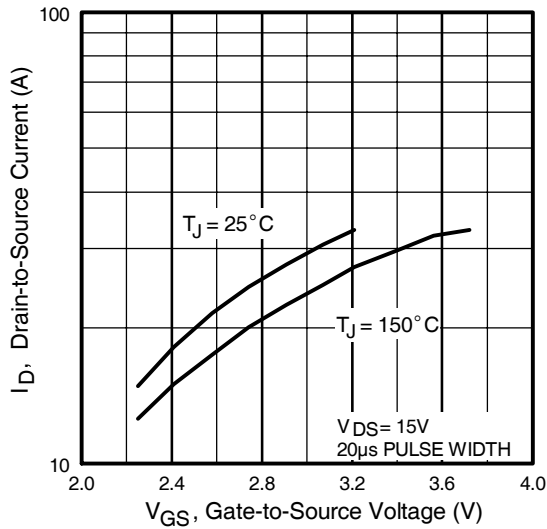
③ Surface mounted on FR-4 board, t ≤ 5sec.



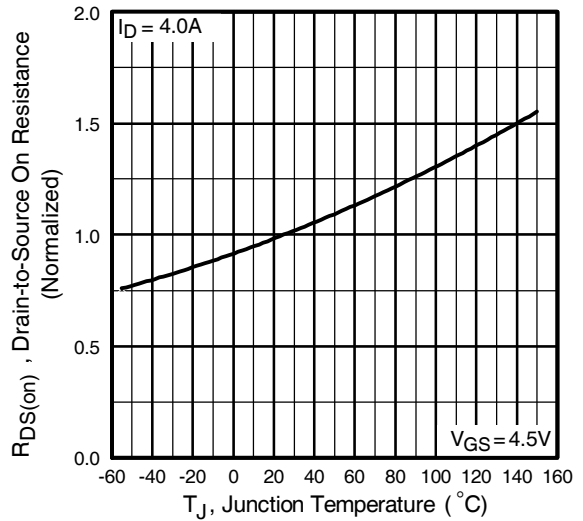
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

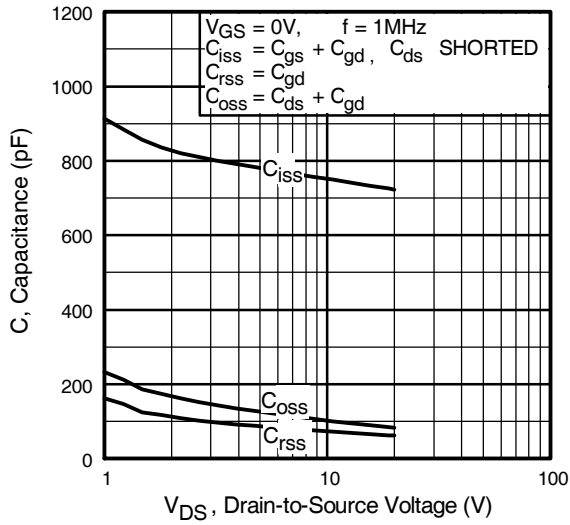


**Fig 3.** Typical Transfer Characteristics

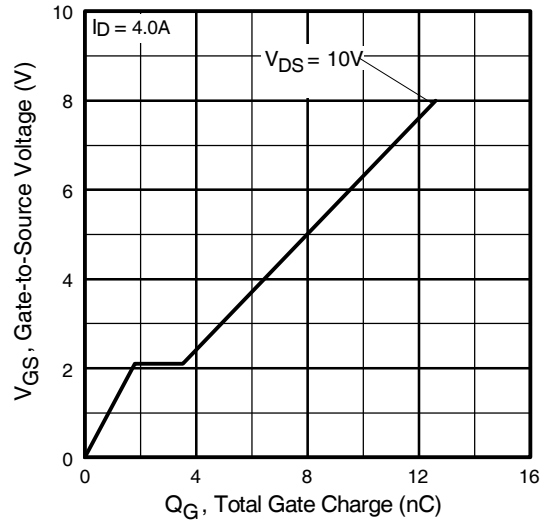


**Fig 4.** Normalized On-Resistance Vs. Temperature

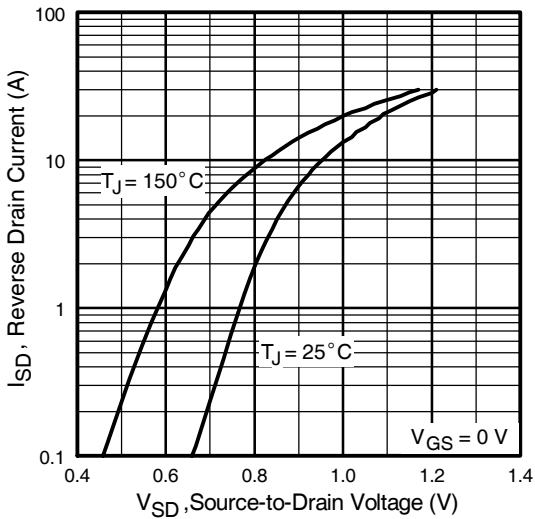
# IRLML2502PbF



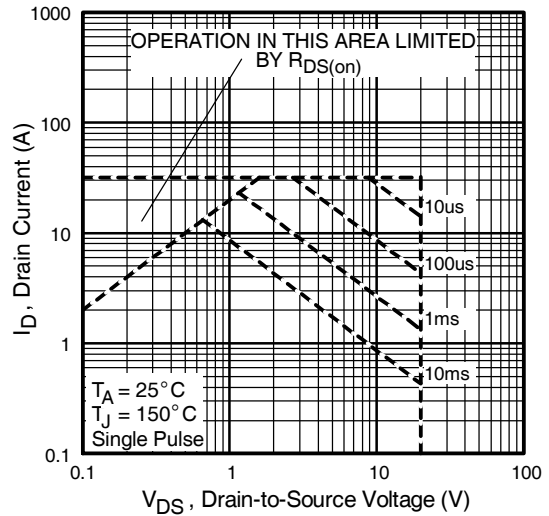
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

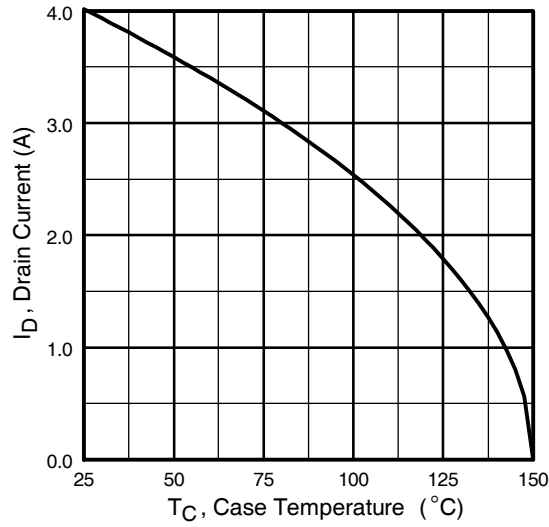


Fig 9. Maximum Drain Current Vs. Case Temperature

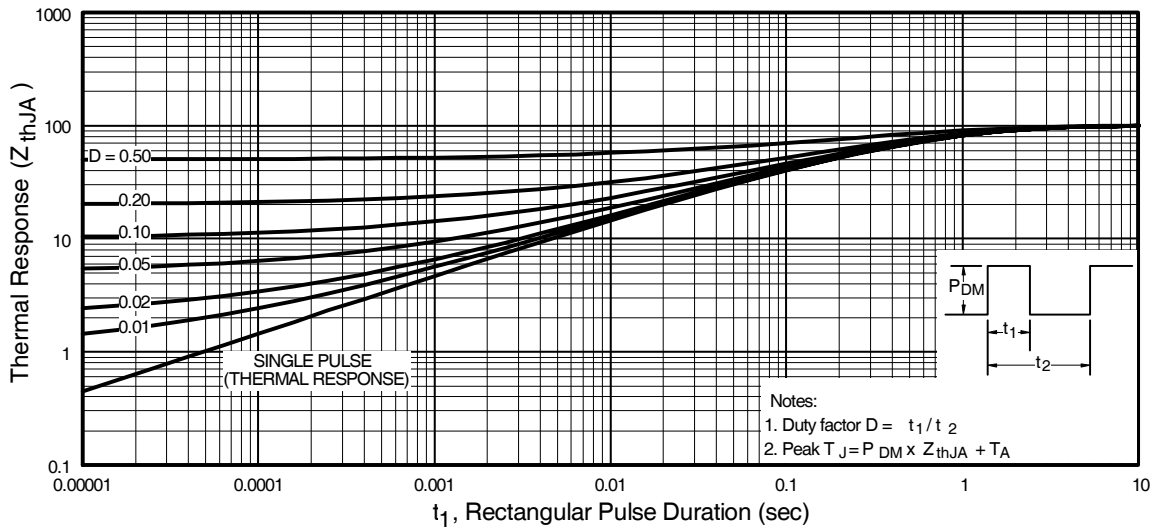


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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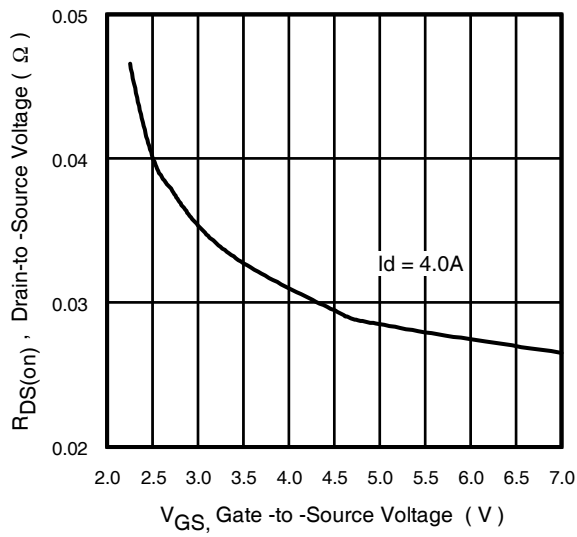


Fig 11. On-Resistance Vs. Gate Voltage

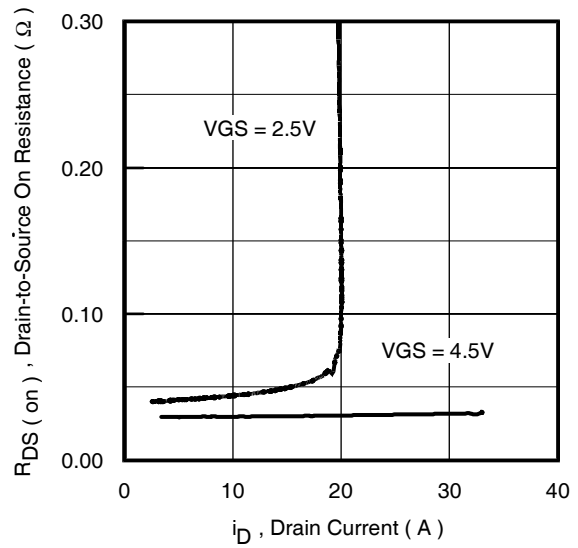
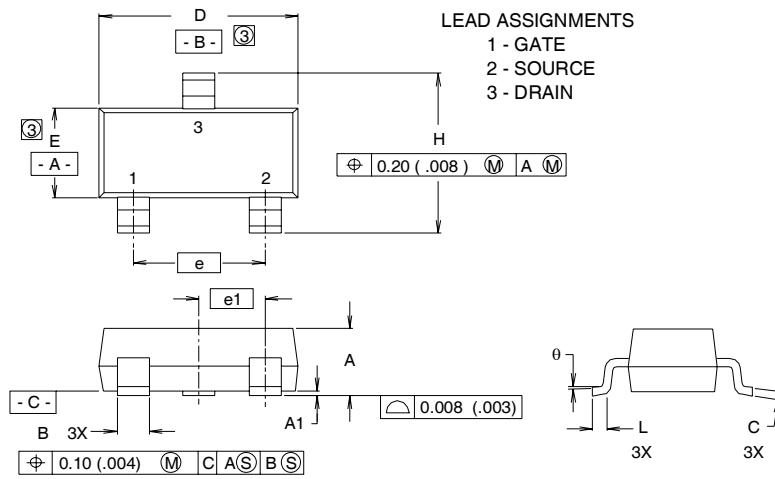


Fig 12. On-Resistance Vs. Drain Current

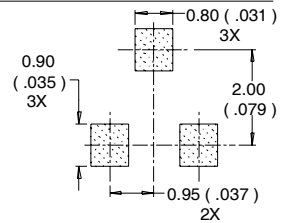
## Micro3™ Package Outline

Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.032	.044	0.82	1.11
A1	.001	.004	0.02	0.10
B	.015	.021	0.38	0.54
C	.004	.006	0.10	0.15
D	.105	.120	2.67	3.05
e	.0750 BASIC		1.90 BASIC	
e1	.0375 BASIC		0.95 BASIC	
E	.047	.055	1.20	1.40
H	.083	.098	2.10	2.50
L	.005	.010	0.13	0.25
$\theta$	0°	8°	0°	8°

### MINIMUM RECOMMENDED FOOTPRINT

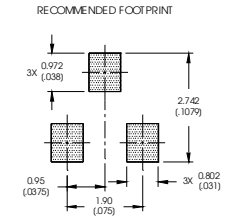
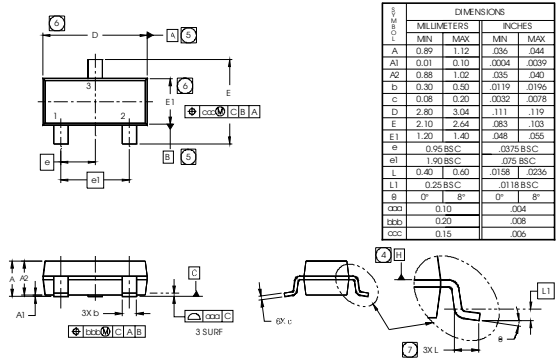


- NOTES:  
 1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.  
 2. CONTROLLING DIMENSION : INCH.  
 ③ DIMENSIONS DO NOT INCLUDE MOLD FLASH.

# IRLML2502PbF

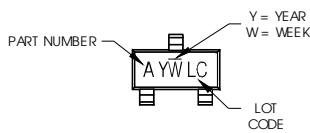
## Micro3 (SOT-23) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS AND INCHES.
  3. CONTROLLING DIMENSION: MILLIMETER.
  - ③ DATUM PLANE B IS LOCATED AT THE MOLD PARTING LINE.
  - ④ DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
  - ⑤ DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H.
  - ⑥ DIMENSION L IS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE.
  8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-236AB.

## Micro3 (SOT-23/TO-236AB) Part Marking Information



PART NUMBER CODE REFERENCE:

- A = IRLML2402
- B = IRLML2803
- C = IRLML6302
- D = IRLML5103
- E = IRLML6402
- F = IRLML6401
- G = IRLML2502
- H = IRLML5203

Note: A line above the work week (as shown here) indicates Lead-Free.

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
1994	4	04	D
1995	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

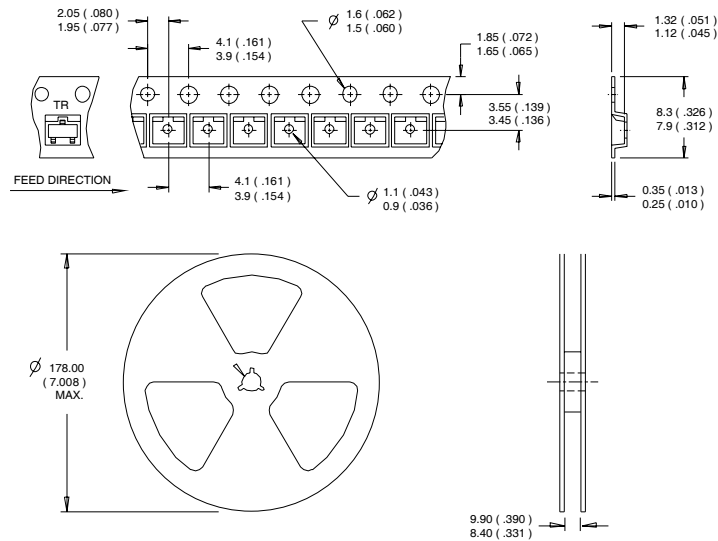
W = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
1994	D	30	D
1995	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z



## Micro3™ Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:  
 1. CONTROLLING DIMENSION : MILLIMETER.  
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.